

# SKM200GB12F4SiC3



## SEMITRANS® 3

### High Speed IGBT4 Modules

#### SKM200GB12F4SiC3

##### Features\*

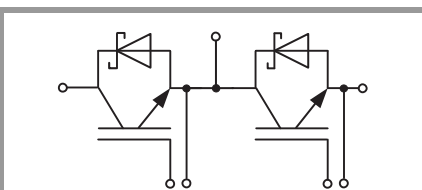
- IGBT4 = 4. Generation Fast Trench (High Speed) IGBT (Infineon)
- With Silicon Carbide Schottky diodes (ROHM)
- Insulated copper baseplate using DBC Technology (Direct Bonded Copper)
- UL recognized, file no. E63532
- With integrated gate resistor
- For higher switching frequencies

##### Typical Applications

- AC inverter drives
- UPS
- Electronic welders
- DC/DC converters

##### Remarks

- Case temperature limited to  $T_c = 125^\circ\text{C}$  max.
- Recommended  $T_{op} = -40 \dots +150^\circ\text{C}$
- Product reliability results valid for  $T_j = 150^\circ\text{C}$



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Absolute Maximum Ratings				
Symbol	Conditions	Values	Unit	
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_C$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	312	A
		$T_c = 80^\circ\text{C}$	239	A
$I_{Cnom}$		200	A	
$I_{CRM}$		400	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$ $R_{G\ on/off} \geq 2\ \Omega$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
	$T_j$			
<b>Inverse diode</b>				
$V_{RRM}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_F$	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	123	A
		$T_c = 80^\circ\text{C}$	93	A
$I_{FRM}$		168	A	
$I_{FSM}$	$t_p = 8.3\text{ ms, sin } 180^\circ, T_j = 25^\circ\text{C}$	295	A	
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Module</b>				
$I_{t(RMS)}$		500	A	
$T_{stg}$		-40 ... 125	$^\circ\text{C}$	
$V_{isol}$	AC sinus 50 Hz, $t = 1\text{ min}$	4000	V	

Characteristics						
Symbol	Conditions	min.	typ.	max.	Unit	
<b>IGBT</b>						
$V_{CE(sat)}$	$I_C = 200\text{ A}$ $V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	2.06	2.42	V	
		$T_j = 150^\circ\text{C}$	2.59	2.97	V	
$V_{CE0}$	chipelevel	$T_j = 25^\circ\text{C}$	1.10	1.28	V	
		$T_j = 150^\circ\text{C}$	0.95	1.13	V	
$r_{CE}$	$V_{GE} = 15\text{ V}$ chipelevel	$T_j = 25^\circ\text{C}$	4.8	5.7	m $\Omega$	
		$T_j = 150^\circ\text{C}$	8.2	9.2	m $\Omega$	
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 7.6\text{ mA}$	5.1	5.8	6.4	V	
$I_{CES}$	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$		2.7	mA	
		$T_j = 150^\circ\text{C}$		-	mA	
$C_{ies}$	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	12.3	nF		
$C_{oes}$		$f = 1\text{ MHz}$	0.81	nF		
$C_{res}$		$f = 1\text{ MHz}$	0.69	nF		
$Q_G$	$V_{GE} = -8\text{ V} \dots +15\text{ V}$		1134	nC		
$R_{Gint}$	$T_j = 25^\circ\text{C}$		2.4	$\Omega$		
$t_{d(on)}$	$V_{CC} = 600\text{ V}$ $I_C = 200\text{ A}$	$T_j = 150^\circ\text{C}$	140	ns		
$t_r$	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$	30	ns		
$E_{on}$	$R_{G\ on} = 1\ \Omega$	$T_j = 150^\circ\text{C}$	3.5	mJ		
$t_{d(off)}$	$R_{G\ off} = 1\ \Omega$	$T_j = 150^\circ\text{C}$	340	ns		
$t_f$	$di/dt_{on} = 7100\text{ A}/\mu\text{s}$ $di/dt_{off} = 2850\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	60	ns		
$E_{off}$		$T_j = 150^\circ\text{C}$	14	mJ		
$R_{th(j-c)}$	per IGBT			0.115	K/W	

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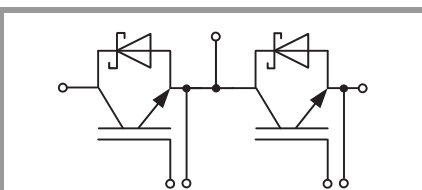
#### Typical Applications

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#### Remarks

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- Product reliability results valid for  $T_j = 150^\circ\text{C}$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverse diode</b>						
$V_F = V_{SD}$	$I_F = 80\text{ A}$ $V_{GE} = 0\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$		1.40	1.60	V
		$T_j = 150^\circ\text{C}$		1.79	2.10	V
$V_{F0}$	chipllevel	$T_j = 25^\circ\text{C}$		0.95	1.05	V
		$T_j = 150^\circ\text{C}$		0.83	0.90	V
$r_F$	chipllevel	$T_j = 25^\circ\text{C}$		5.6	6.9	m $\Omega$
		$T_j = 150^\circ\text{C}$		12	15	m $\Omega$
$C_j$	f = 1 MHz, $V_R = 800\text{ V}$ , $T_j = 25^\circ\text{C}$ , parallel to $C_{oss}$			0.34		nF
$Q_c$	$V_R = 800\text{ V}$ , $di/dt_{off} = 6200\text{ A}/\mu\text{s}$			0.26		$\mu\text{C}$
$R_{th(j-c)}$	per diode				0.42	K/W
<b>Module</b>						
$L_{CE}$				15		nH
$R_{CC'+EE'}$	measured per switch	$T_c = 25^\circ\text{C}$		0.55		m $\Omega$
		$T_c = 125^\circ\text{C}$		0.85		m $\Omega$
$R_{th(c-s)1}$	calculated without thermal coupling ( $\lambda_{grease} = 0.81\text{ W}/(\text{m}^2\text{K})$ )			0.02	0.038	K/W
$M_s$	to heat sink M6		3		5	Nm
$M_t$		to terminals M6	2.5		5	Nm
						Nm
$W$					325	g



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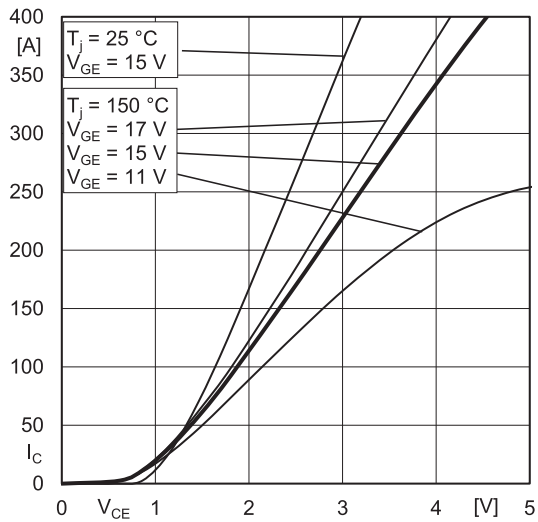


Fig. 1: Typ. output characteristic, inclusive  $R_{CC'+EE'}$

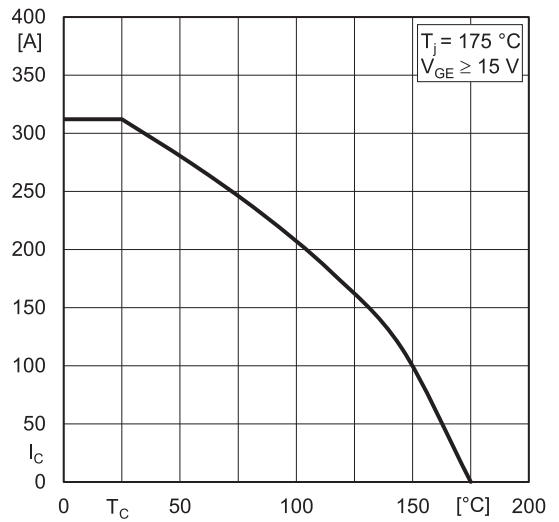


Fig. 2: Rated current vs. temperature  $I_C = f(T_C)$

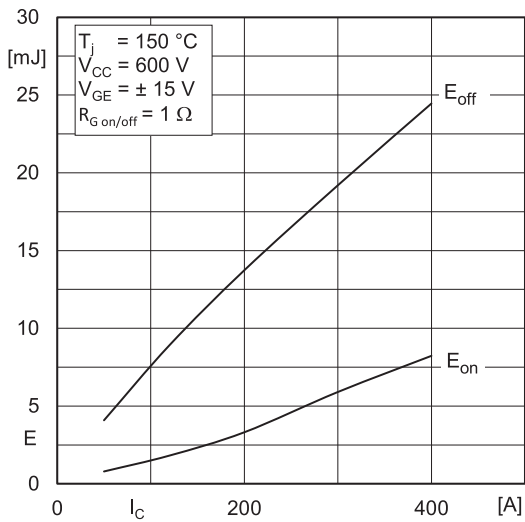


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

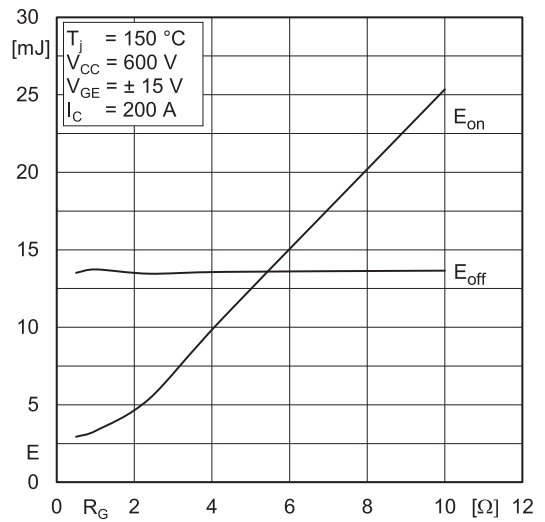


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

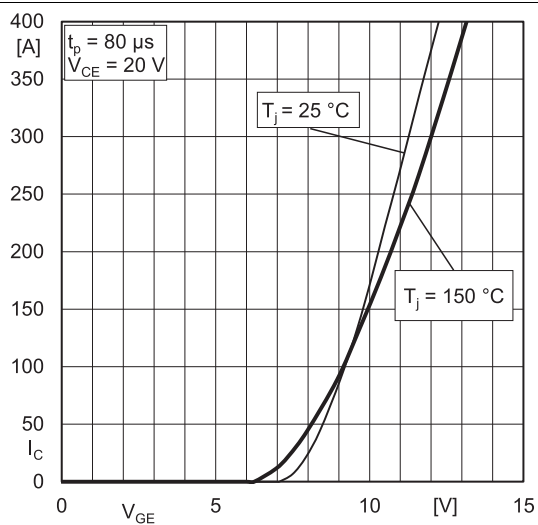


Fig. 5: Typ. transfer characteristic

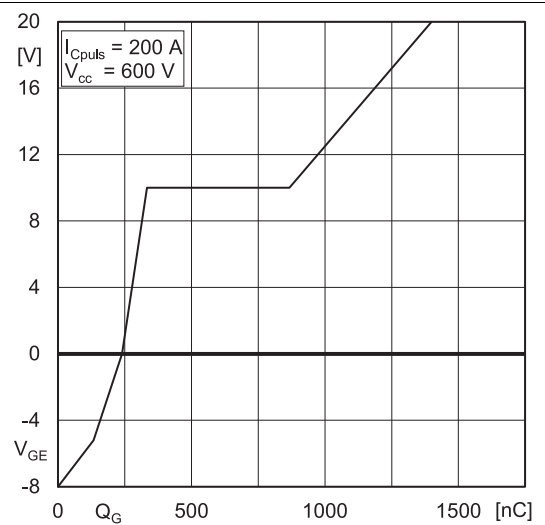


Fig. 6: Typ. gate charge characteristic

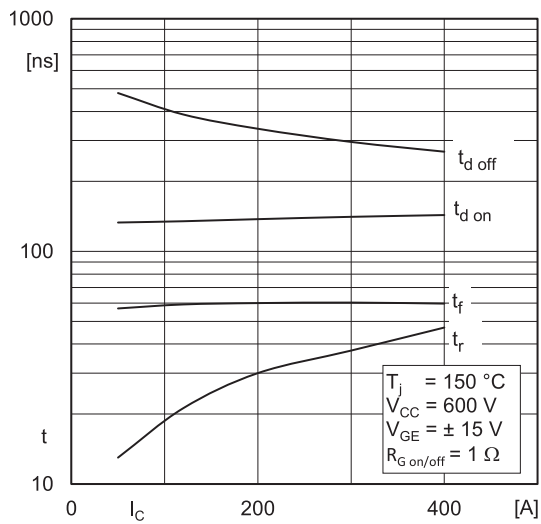


Fig. 7: Typ. switching times vs.  $I_C$

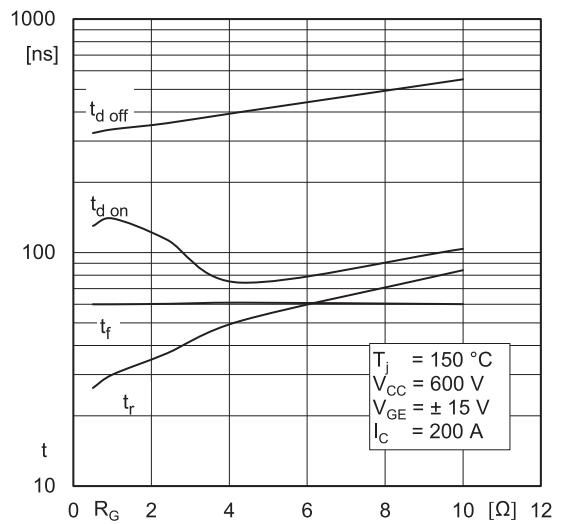


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

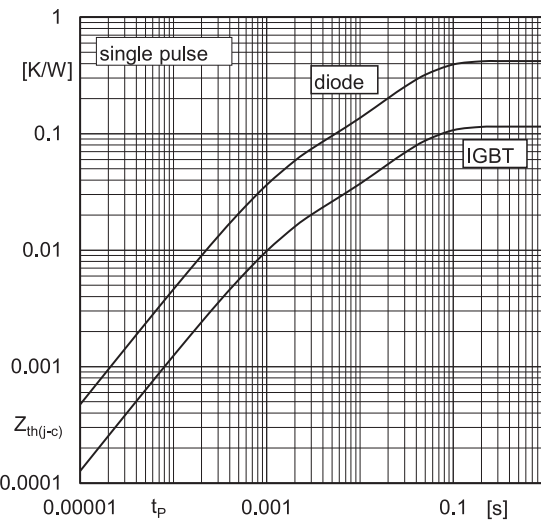


Fig. 9: Transient thermal impedance

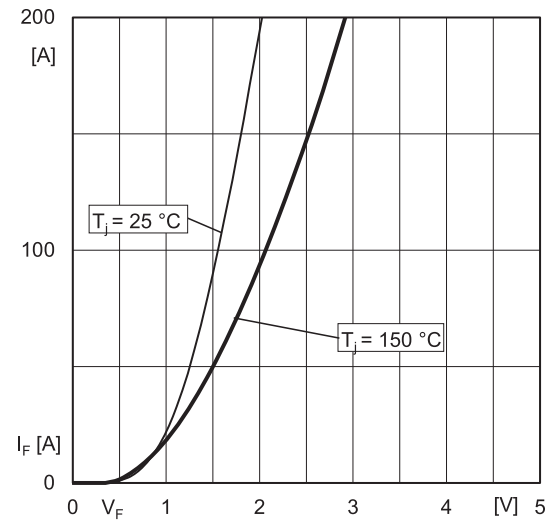
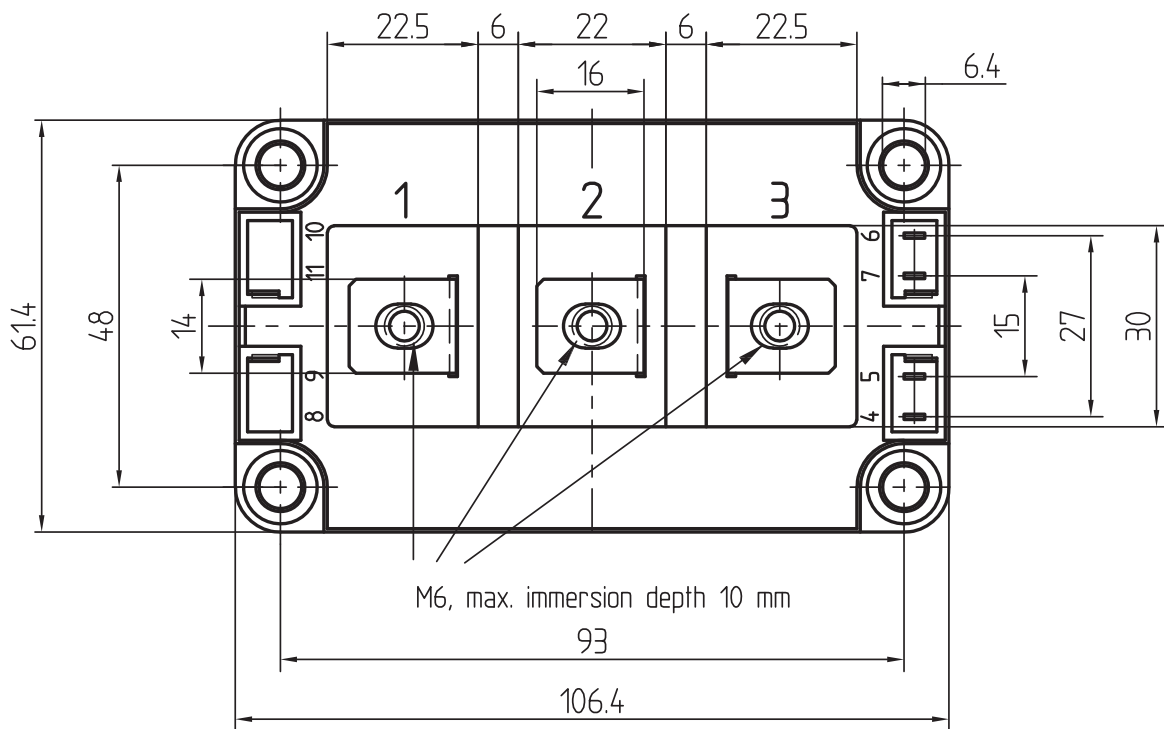
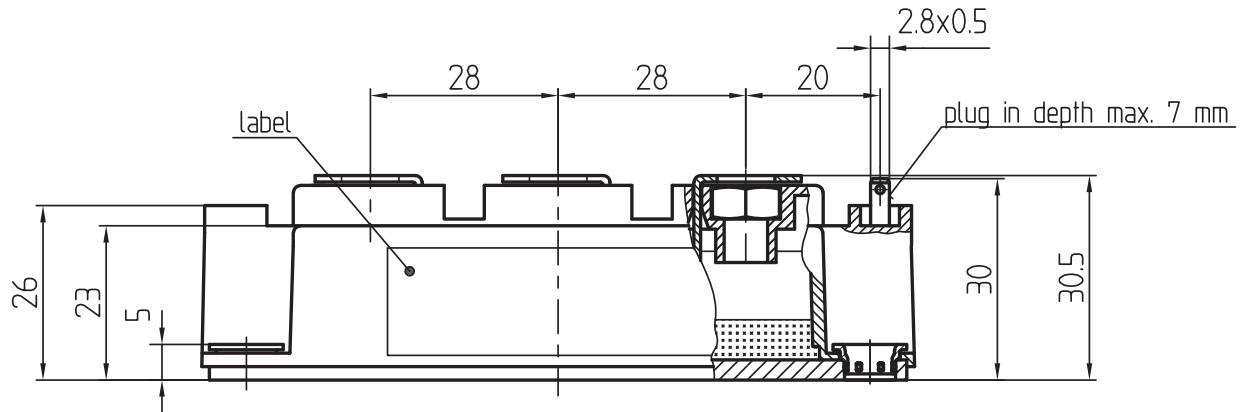


Fig. 10: Typ. Diode forward charact., incl.  $R_{CC+EE}$

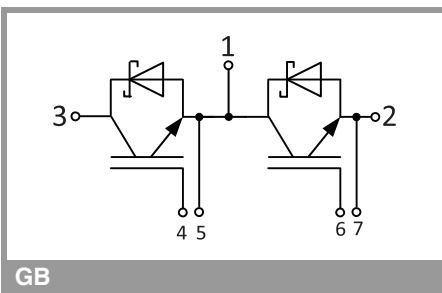
# SKM200GB12F4SiC3

Dimensions in mm



General tolerance +/- 0.5 mm

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This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

## **\*IMPORTANT INFORMATION AND WARNINGS**

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